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(54) **LOW-COST COMPLEMENTARY BICMOS INTEGRATION SCHEME**

(71) Applicant: **Newport Fab, LLC**, Newport Beach, CA (US)

(72) Inventors: **Edward Preisler**, San Clemente, CA (US); **Todd Thibeault**, Irvine, CA (US)

(73) Assignee: **Newport Fab, LLC**, Newport Beach, CA (US)

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(52) **U.S. Cl.**

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(58) **Field of Classification Search**

CPC H01L 27/0623; H01L 27/102; H01L 27/1022; H01L 21/8249

See application file for complete search history.

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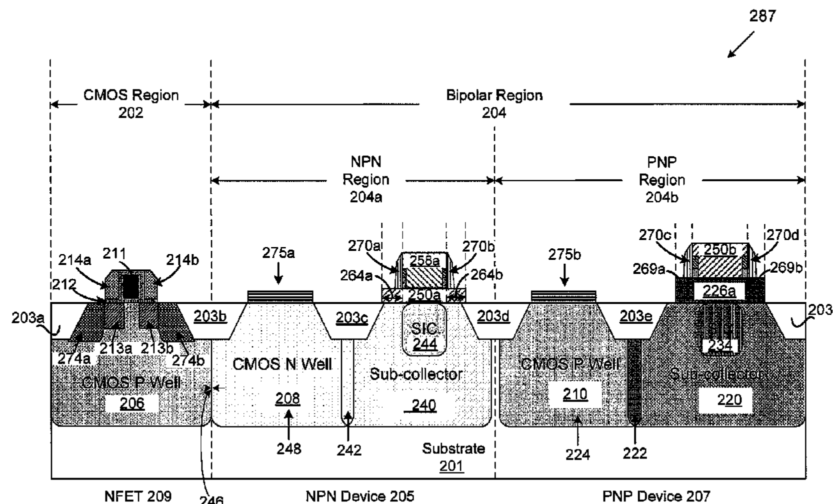
Primary Examiner — Phat X Cao

(74) *Attorney, Agent, or Firm* — Farjami & Farjami LLP

(57) **ABSTRACT**

A bipolar complementary-metal-oxide-semiconductor (BiCMOS) device is disclosed. The BiCMOS device includes a CMOS device in a CMOS region, a first CMOS well in the CMOS region, an NPN bipolar device in a bipolar region, a second CMOS well in the bipolar region, the second CMOS well being a collector sinker and being electrically connected to a sub-collector of the NPN bipolar device, where the first CMOS well in the CMOS region and the second CMOS well in the bipolar region form a p-n junction to provide electrical isolation between the CMOS device and the NPN bipolar device. The BiCMOS device further includes a PNP bipolar device having a sub-collector, the sub-collector of the PNP bipolar device being electrically connected to a third CMOS well.

18 Claims, 8 Drawing Sheets



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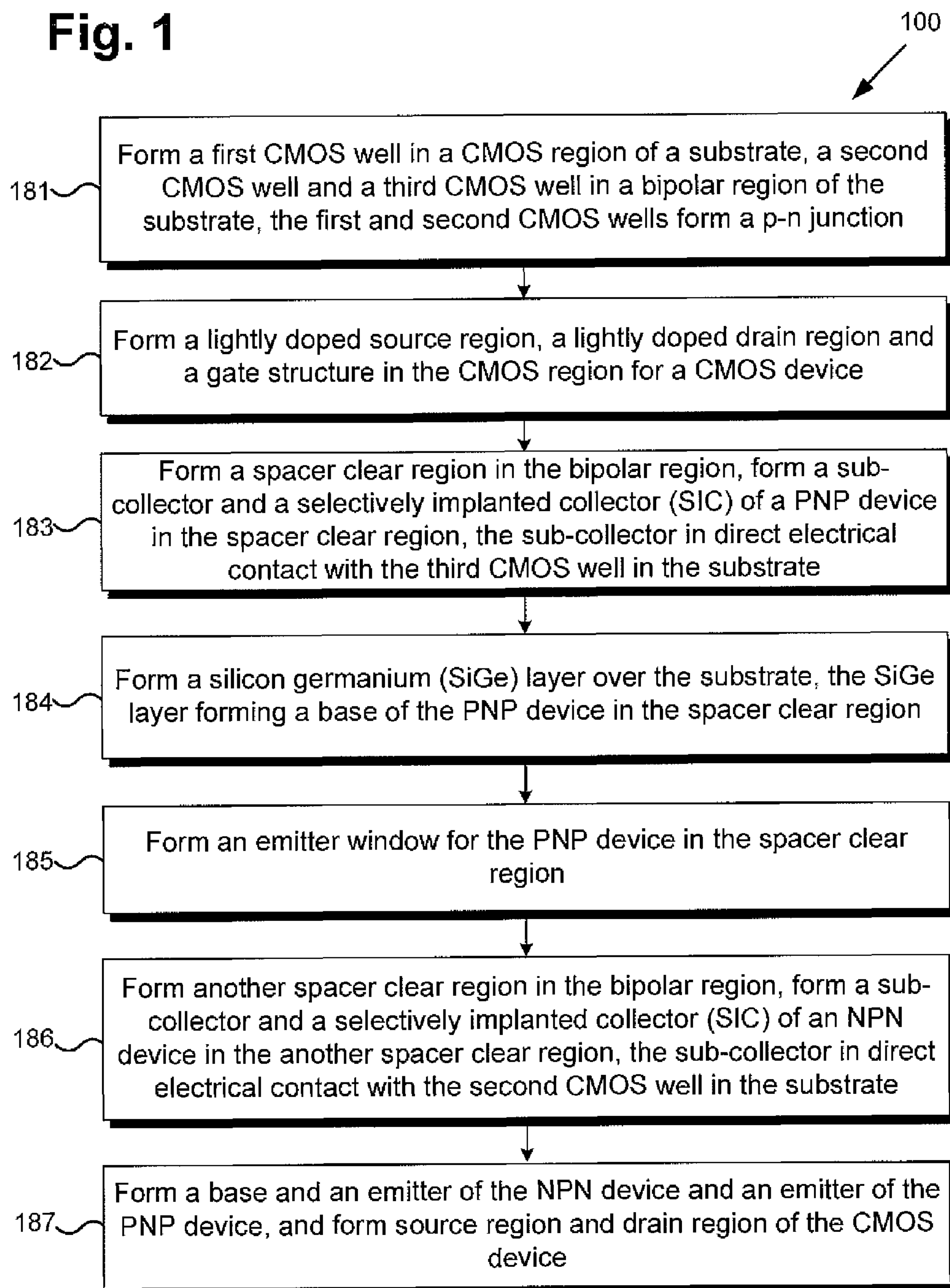
Fig. 1
100
181
Form a first CMOS well in a CMOS region of a substrate, a second CMOS well and a third CMOS well in a bipolar region of the substrate, the first and second CMOS wells form a p-n junction
182
Form a lightly doped source region, a lightly doped drain region and a gate structure in the CMOS region for a CMOS device
183
Form a spacer clear region in the bipolar region, form a sub-collector and a selectively implanted collector (SIC) of a PNP device in the spacer clear region, the sub-collector in direct electrical contact with the third CMOS well in the substrate
184
Form a silicon germanium (SiGe) layer over the substrate, the SiGe layer forming a base of the PNP device in the spacer clear region
185
Form an emitter window for the PNP device in the spacer clear region
186
Form another spacer clear region in the bipolar region, form a sub-collector and a selectively implanted collector (SIC) of an NPN device in the another spacer clear region, the sub-collector in direct electrical contact with the second CMOS well in the substrate
187
Form a base and an emitter of the NPN device and an emitter of the PNP device, and form source region and drain region of the CMOS device

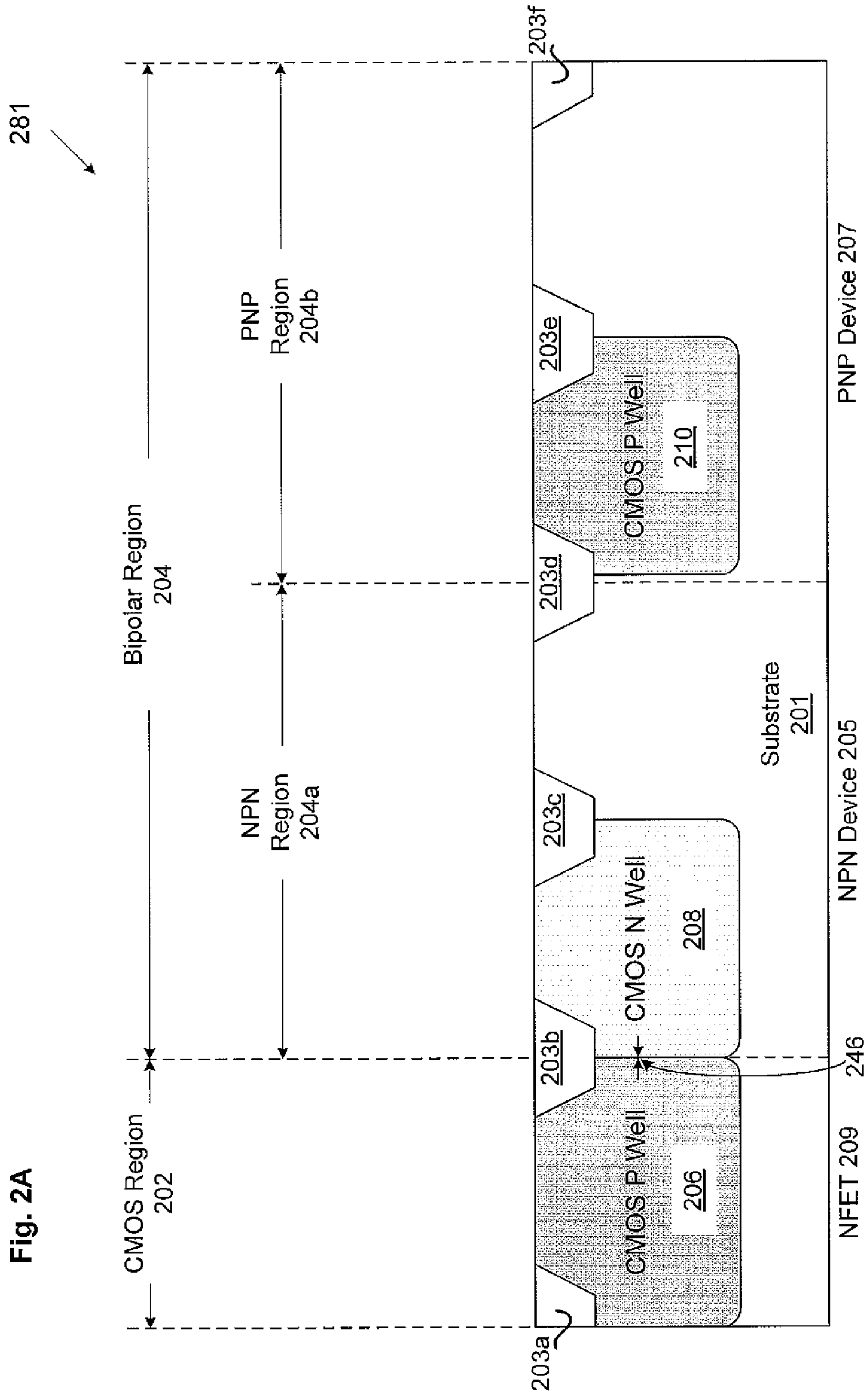
Fig. 2A
281
CMOS Region
202
Bipolar Region
204
NPN
Region
204a
PNP
Region
204b
203a
203b
203c
203d
203e
203f
CMOS P Well
206
CMOS N Well
208
CMOS P Well
210
246
Substrate
201
NFET 209
NPN Device 205
PNP Device 207

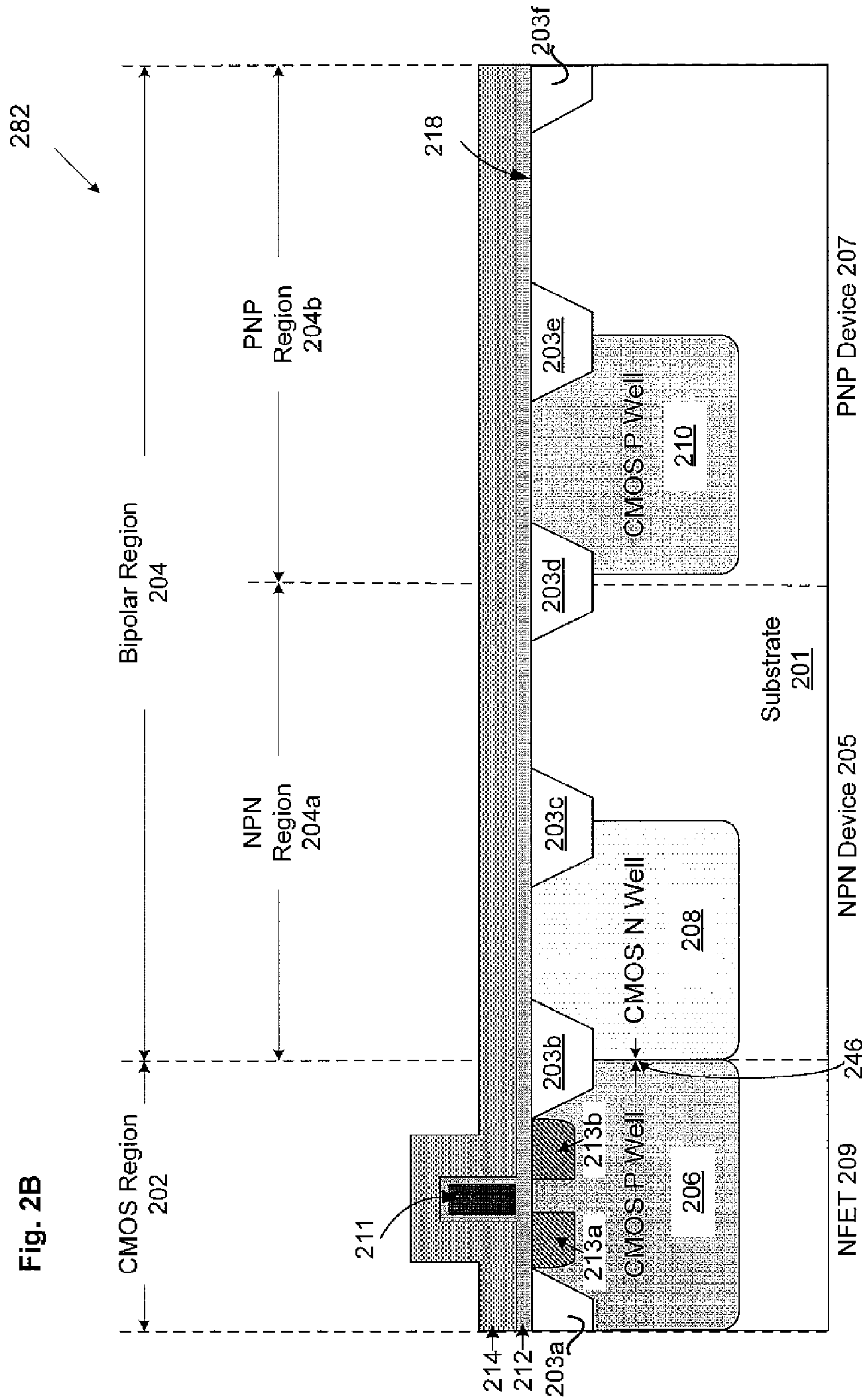
Fig. 2B
282
CMOS Region 202
Bipolar Region 204
NPN Region 204a
PNP Region 204b
211
218
203f
214
212
203a
213a
213b
203b
203c
203d
203e
CMOS P Well
206
CMOS N Well
208
CMOS P Well
210
Substrate
201
246
NFET 209
NPN Device 205
PNP Device 207

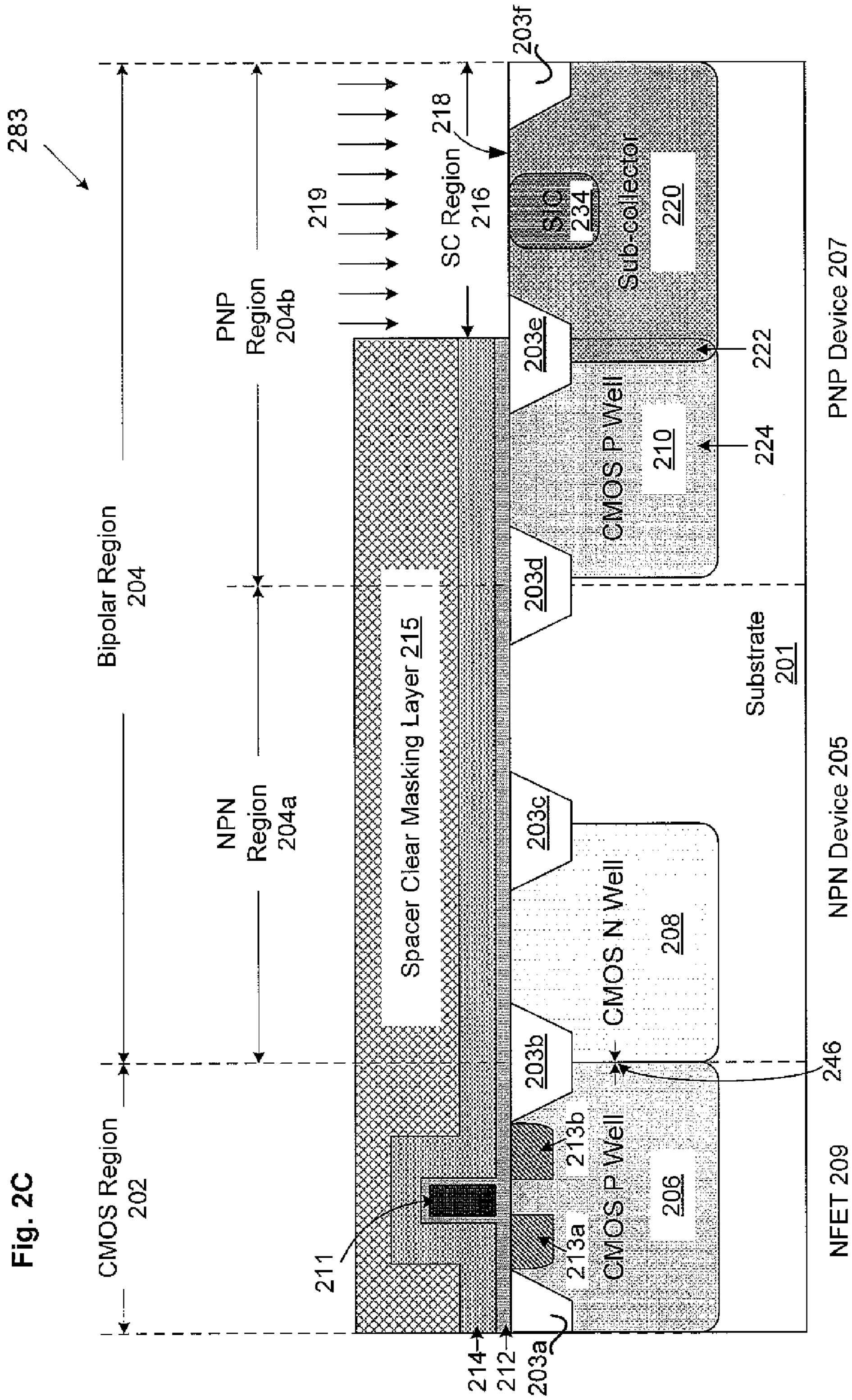
Fig. 2C
283
CMOS Region 202
Bipolar Region 204
NPN Region 204a
PNP Region 204b
219
SC Region 216
218
203f
SIO 234
Sub-collector 220
203e
222
CMOS P Well 210
224
203d
Substrate 201
PNP Device 207
Spacer Clear Masking Layer 215
203c
CMOS N Well 208
NPN Device 205
203b
246
213b
213a
CMOS P Well 206
NFET 209
211
214
212
203a

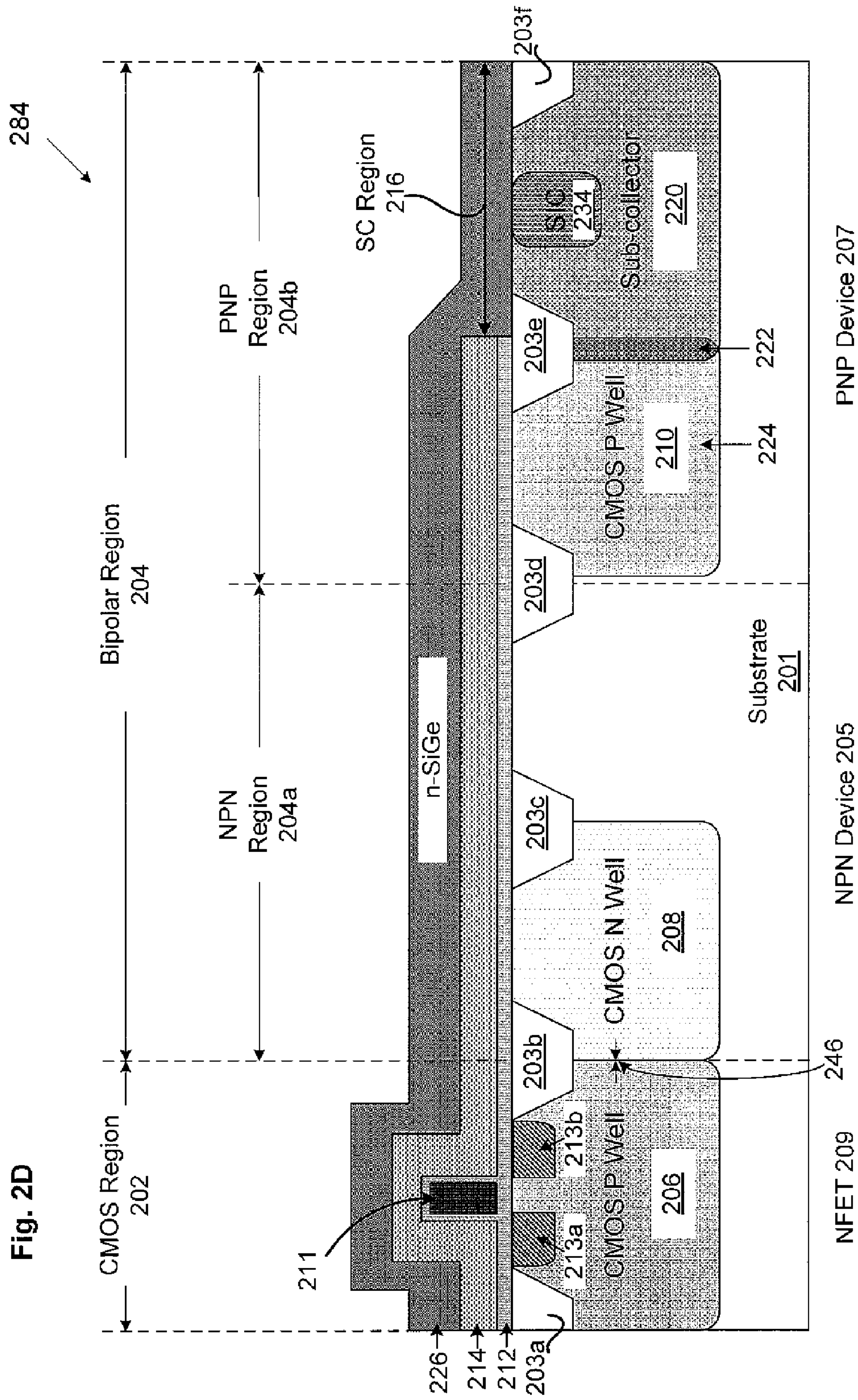
Fig. 2D
284
CMOS Region
202
Bipolar Region
204
NPN
Region
204a
PNP
Region
204b
SC Region
216
203f
SiC
234
Sub-collector
220
222
224
203e
CMOS P Well
210
203d
Substrate
201
n-SiGe
203c
CMOS N Well
208
203b
246
213b
CMOS P Well
206
213a
211
226
214
212
203a
NFET 209
NPN Device 205
PNP Device 207

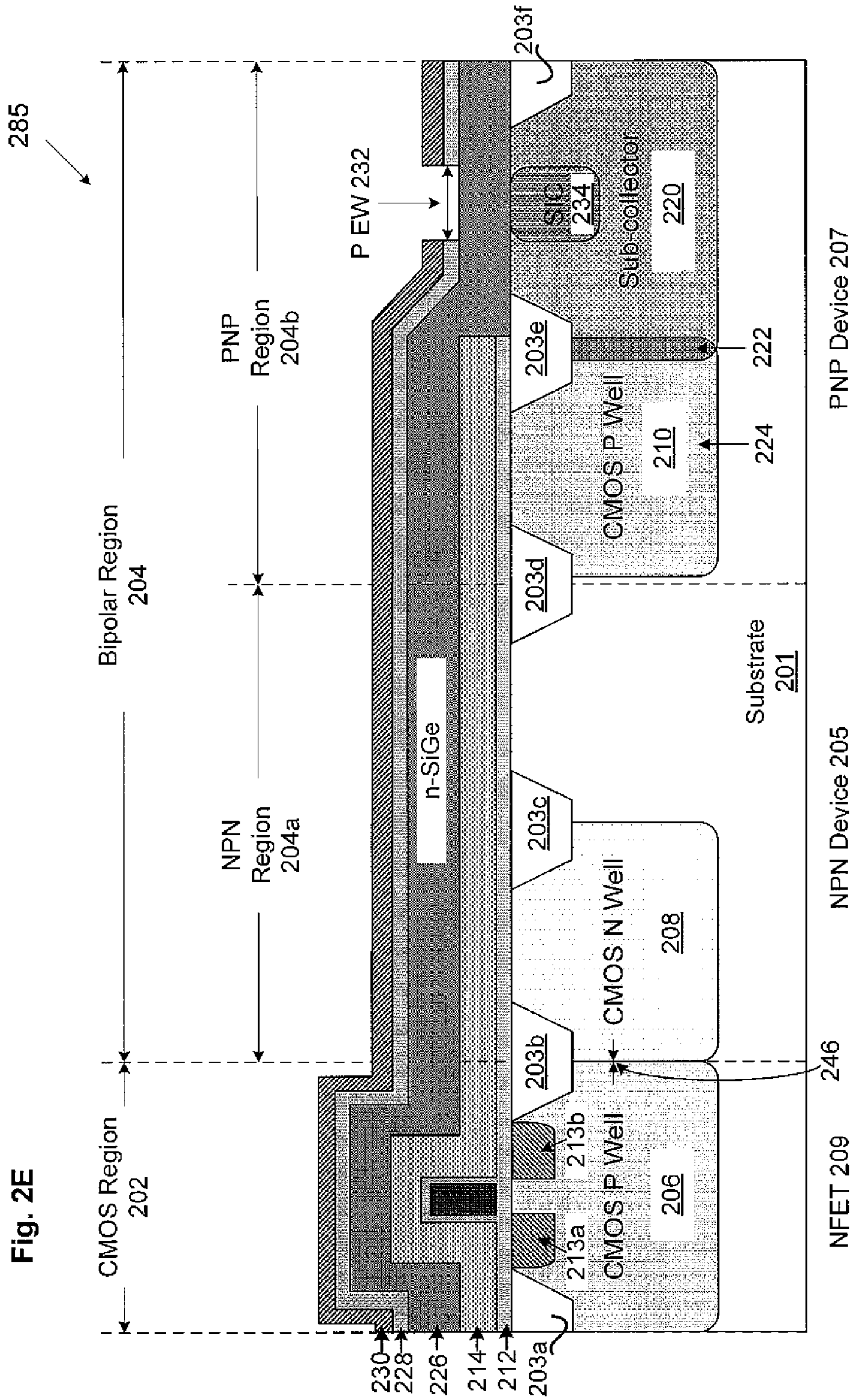
Fig. 2E
285
CMOS Region 202
Bipolar Region 204
NPN Region 204a
PNP Region 204b
P EW 232
203f
SIC 234
Sub-collector 220
203e
222
CMOS P Well 210
224
PNP Device 207
203d
Substrate 201
n-SiGe
203c
CMOS N Well 208
NPN Device 205
203b
246
213b
213a
CMOS P Well 206
NFET 209
230
228
226
214
212
203a

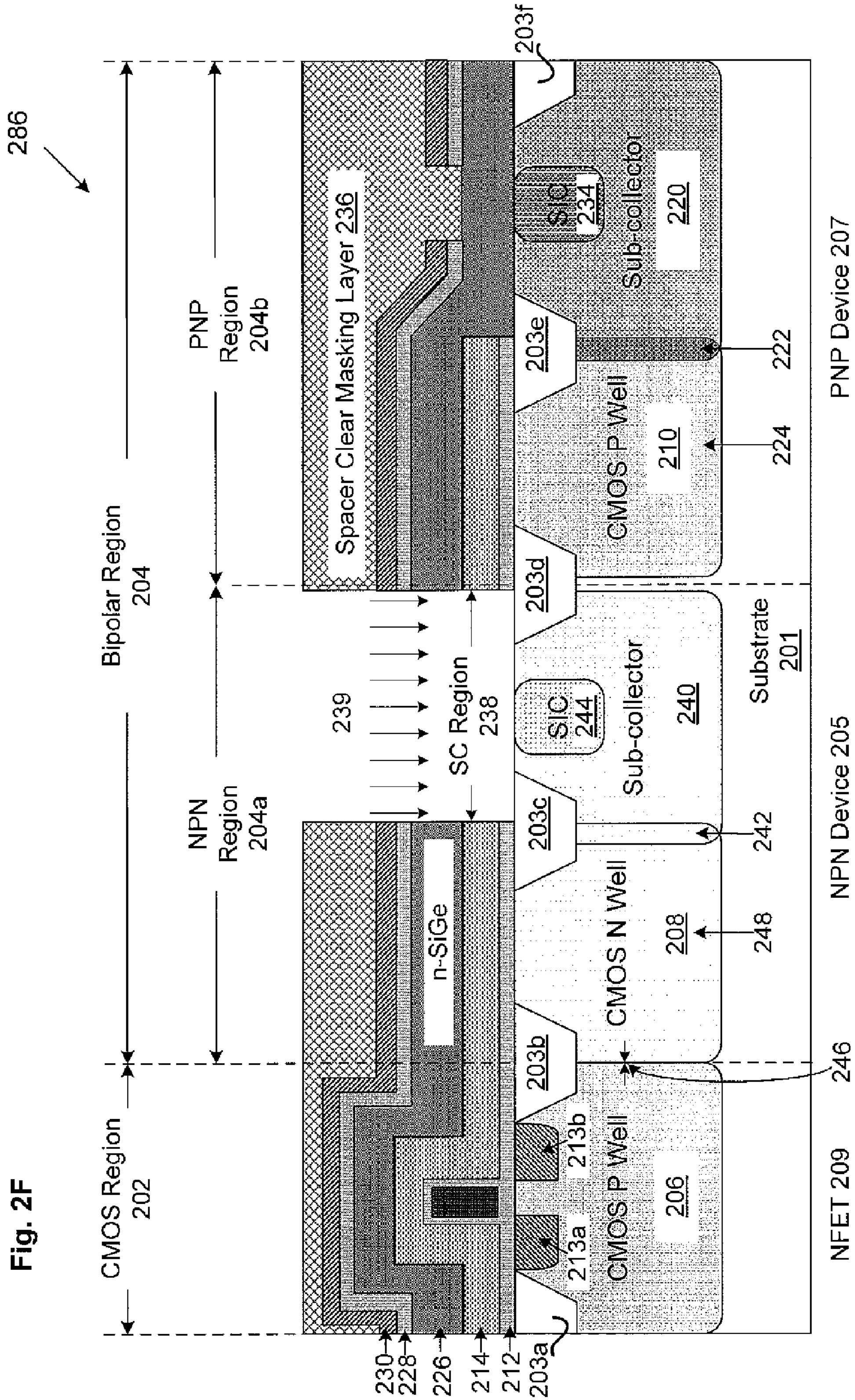
Fig. 2F
286
CMOS Region
202
Bipolar Region
204
NPN
Region
204a
PNP
Region
204b
Spacer Clear Masking Layer 236
n-SiGe
239
SC Region
238
203a
203b
203c
203d
203e
203f
213a
213b
SIC
234
Sub-collector
220
SIC
244
Sub-collector
240
CMOS P Well
206
CMOS N Well
208
CMOS P Well
210
Substrate
201
222
224
242
246
248
230
228
226
214
212
NFET 209
NPN Device 205
PNP Device 207

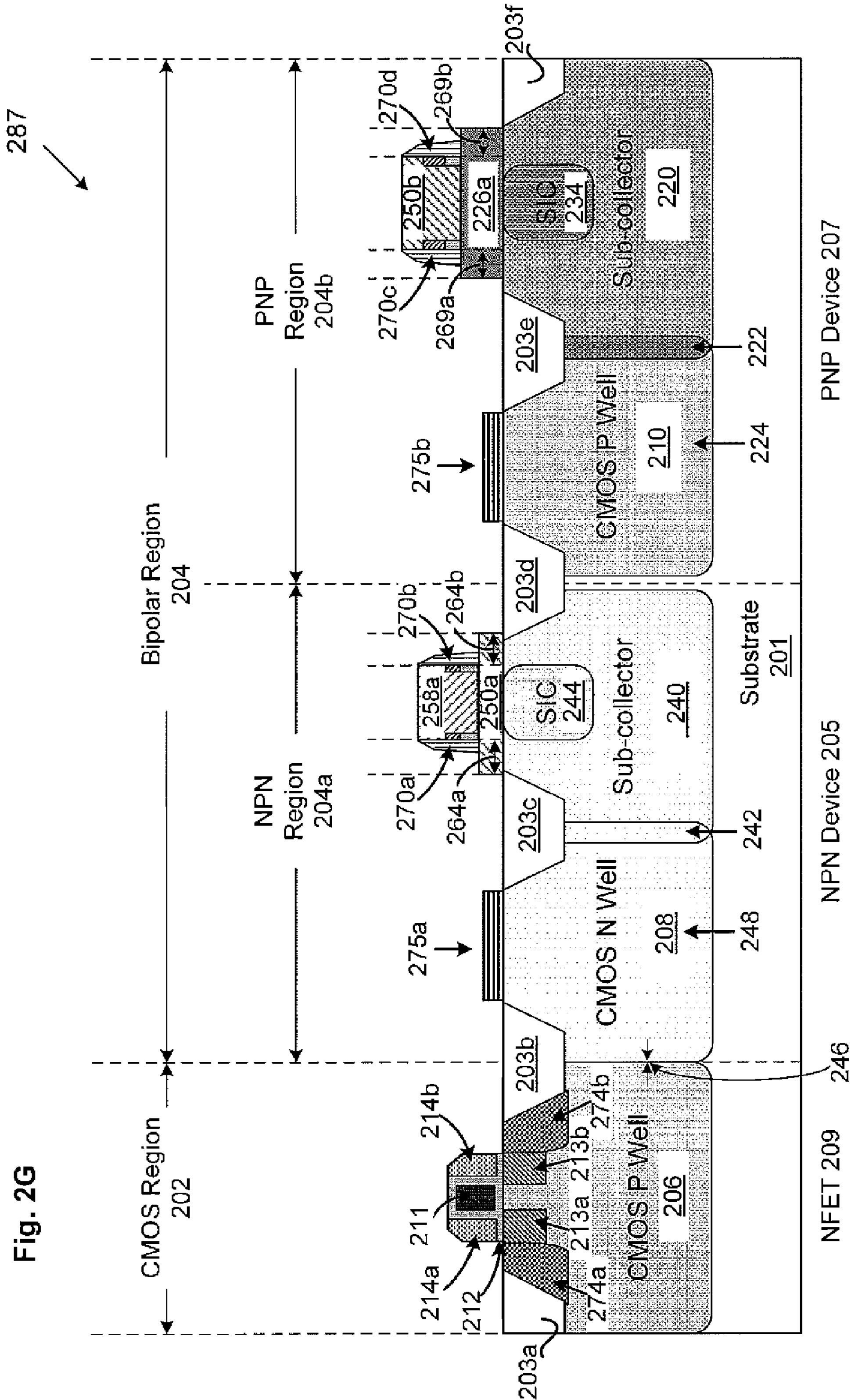
Fig. 2G
287
CMOS Region
202
Bipolar Region
204
NPN
Region
204a
PNP
Region
204b
214a
212
211
214b
213a
213b
274a
274b
203a
203b
203c
203d
203e
203f
CMOS P Well
206
CMOS N Well
208
CMOS P Well
210
246
248
275a
275b
270a
270b
270c
270d
264a
264b
269a
269b
258a
250a
250b
226a
SIC
244
SIC
234
Sub-collector
240
Sub-collector
220
242
222
224
Substrate
201
NFET 209
NPN Device 205
PNP Device 207

LOW-COST COMPLEMENTARY BICMOS INTEGRATION SCHEME

The present application claims the benefit of and priority to a provisional patent application entitled "Low-Cost Complementary BiCMOS Integration Scheme", Ser. No. 61/980,185 filed on Apr. 16, 2014. The disclosure in this provisional application is hereby incorporated fully by reference into the present application.

BACKGROUND

In complementary bipolar complementary-metal-oxide semiconductor (BiCMOS) fabrication processes, bipolar devices and complementary-metal-oxide-semiconductor (CMOS) devices are integrated on the same semiconductor substrate. High performance bipolar devices, such as NPN and PNP silicon-germanium (SiGe) bipolar transistors, require a high mask count when integrated on the same semiconductor substrate as the CMOS devices. As BiCMOS technology continues to advance in an effort to achieve high performance, such as increased speed, frequency response and gain, and reduced power consumption, semiconductor manufacturers are challenged to provide a complementary BiCMOS process that effectively integrates higher performing bipolar and CMOS devices.

In one approach of complementary BiCMOS process flow, when forming a bipolar device, a buried sub-collector layer is formed below and in contact with a collector region and away from a top surface of a semiconductor substrate. A collector sinker extends from the top surface of the semiconductor substrate down to the buried sub-collector layer. The buried sub-collector layer and the collector sinker may provide an electrical pathway from the collector to a collector contact for external connection. However, the formations of the buried sub-collector layers for the NPN and PNP devices require several implanting steps and masking layers. The formations of the collector sinkers for the NPN and PNP devices also require separate implanting steps and masking layers. These steps in the complementary BiCMOS process flow undesirably add to processing complexity and manufacturing cost. Also, deep trench isolation regions may be required to provide electrical isolation for bipolar devices from other devices, such as CMOS devices, fabricated on the semiconductor substrate. The deep trench isolation regions unavoidably occupy the limited usable space on the semiconductor substrate.

Thus, there is a need in the art for a complementary BiCMOS process for effectively integrating complementary bipolar devices, such as SiGe NPN and PNP devices, with CMOS devices without undesirably increasing processing complexity and manufacturing cost.

SUMMARY

The present disclosure is directed to a low-cost complementary BiCMOS integration scheme, substantially as shown in and/or described in connection with at least one of the figures, and as set forth in the claims.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. **1** is a flowchart illustrating a method for fabricating a bipolar complementary-metal-oxide-semiconductor (BiCMOS) device according to one implementation of the present application.

FIG. **2**A illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with an initial action in the flowchart of FIG. **1** according to one implementation of the present application.

FIG. **2**B illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with an intermediate action in the flowchart of FIG. **1** according to one implementation of the present application.

FIG. **2**C illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with an intermediate action in the flowchart of FIG. **1** according to one implementation of the present application.

FIG. **2**D illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with an intermediate action in the flowchart of FIG. **1** according to one implementation of the present application.

FIG. **2**E illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with an intermediate action in the flowchart of FIG. **1** according to one implementation of the present application.

FIG. **2**F illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with an intermediate action in the flowchart of FIG. **1** according to one implementation of the present application.

FIG. **2**G illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with a final action in the flowchart of FIG. **1** according to one implementation of the present application.

DESCRIPTION OF EXEMPLARY IMPLEMENTATIONS

The following description contains specific information pertaining to implementations in the present disclosure. The drawings in the present application and their accompanying detailed description are directed to merely exemplary implementations. Unless noted otherwise, like or corresponding elements among the figures may be indicated by like or corresponding reference numerals. Moreover, the drawings and illustrations in the present application are generally not to scale, and are not intended to correspond to actual relative dimensions.

FIG. **1** shows an exemplary diagram illustrating an exemplary method for fabricating a bipolar complementary-metal-oxide-semiconductor (BiCMOS) device, according to one implementation of the present inventive concepts. Certain details and features have been left out of flowchart **100** that are apparent to a person of ordinary skill in the art. For example, an action may comprise one or more sub actions or may involve specialized equipment or materials, as is known in the art. While actions **181** through **187** indicated in flowchart **100** are sufficient to describe one implementation disclosed herein, other implementations disclosed herein may use actions different from those shown in flowchart **100**.

As illustrated in flowchart **100**, action **181** includes forming a first CMOS well in a CMOS region of a substrate, a second CMOS well and a third CMOS well in a bipolar region of the substrate, where the first and second CMOS wells form a p-n junction. Action **182** includes forming a lightly doped source region, a lightly doped drain region, and a gate structure in the CMOS region for a CMOS device. Action **183** includes forming a spacer clear region in the bipolar region, and forming a sub-collector, and a selectively implanted collector (SIC) (also known and referred to in the art simply as a "collector") of a PNP device in the spacer clear region, where the sub-collector is in direct electrical

contact with the third CMOS well in the substrate. Action **184** includes forming a silicon germanium (SiGe) layer over the substrate, the SiGe layer forming a base of the PNP device in the spacer clear region. Action **185** includes forming an emitter window for the PNP device in the spacer clear region. Action **186** includes forming another spacer clear region in the bipolar region, and forming a sub-collector, and a selectively implanted collector (SIC) (also known and referred to in the art simply as a "collector") of an NPN device in the another spacer clear region, where the sub-collector is in direct electrical contact with the second CMOS well in the substrate. Action **187** includes forming a base and an emitter of the NPN device and an emitter of the PNP device, and forming source region and drain region of the CMOS device.

FIGS. **2**A through **2**G and structures **281** through **287** illustrate the result of performing actions **181** through **187** of flowchart **100** of FIG. **1**, respectively, according to one implementation of the present disclosure. For example, structure **281** shows a semiconductor structure after action **181**, structure **282** shows structure **281** after action **182**, structure **283** shows structure **282** after action **183**, and so forth. FIG. **2**G illustrates a cross-sectional view of a portion of a semiconductor structure processed in accordance with final action **187** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure.

Referring to FIG. **2**A, structure **281** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **181** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As shown in FIG. **2**A, structure **281** includes semiconductor substrate **201**, CMOS P well **206**, CMOS N well **208**, CMOS P well **210**, and isolation regions **203***a*, **203***b*, **203***c*, **203***d*, **203***e* and **203***f*. Semiconductor substrate **201** may include a lightly doped P type silicon or other appropriate substrate material. Isolation regions **203***a*, **203***b*, **203***c*, **203***d*, **203***e* and **203***f* are situated in semiconductor substrate **201**, and may include field oxide, such as silicon oxide. Isolation regions **203***a*, **203***b*, **203***c*, **203***d*, **203***e* and **203***f* can include shallow trench isolation (STI) regions, and can be formed in any manner known in the art.

As illustrated in FIG. **2**A, CMOS P well **206**, CMOS N well **208** and CMOS P well **210** are formed in semiconductor substrate **201** in CMOS region **202**, NPN region **204***a* and PNP region **204***b*, respectively. For example, CMOS P wells **206** and **210** can be formed by utilizing a well mask to define respective portions of semiconductor substrate **201** in CMOS region **202** and bipolar region **204**, and implanting boron or other appropriate P type dopant in the defined portions of semiconductor substrate **201**. Thus, CMOS P well **210** in PNP region **204***b* can be formed at the same time, using the same well mask and the same type dopant as other CMOS P wells, such as CMOS P well **206**, in CMOS region **202**. In one implementation, CMOS P wells **206** and **210** may include a heavily doped P type implant. As discussed below, CMOS P well **206** can be utilized as the well region for N-channel field-effect transistor (NFET) **209**. Also, CMOS P well **210** can be utilized as a collector sinker for PNP device **207** in PNP region **204***b*.

CMOS N well **208** in NPN region **204***a* and other CMOS N wells in CMOS region **202** (not explicitly shown in FIG. **2**A) can be formed by utilizing a well mask to define respective portions of semiconductor substrate **201** in NPN region **204***a* and CMOS region **202**, and implanting phosphorus or other appropriate N type dopant in the defined portions of semiconductor substrate **201**. CMOS N well **208** in NPN region **204***a* can be formed at the same time, using

the same well mask and using the same type dopant, as other CMOS N wells in CMOS region **202**. In one implementation, CMOS N well **208** may include a heavily doped N type implant. As discussed below, CMOS N well **208** can be utilized as a collector sinker for NPN device **205** in NPN region **204***a*.

As illustrated in FIG. **2**A, CMOS P well **206** and CMOS N well **208** form p-n junction **246** to provide electrical isolation between NFET **209** and NPN device **205**. Since p-n junction **246** provides electrical isolation between CMOS P well **206** and CMOS N well **208**, additional isolations structures, such as deep trench isolation structures, are not required between NFET **209** and NPN device **205**, thereby saving usable space on semiconductor substrate **201** and reducing manufacturing cost. In another implementation, CMOS P well **206** may be spaced apart from CMOS N well **208** to provide electrical isolation between NFET **209** and NPN device **205**.

Although FIG. **2**A illustrates the formations of CMOS P well **206**, CMOS N well **208**, CMOS P well **210**, it should be understood that additional CMOS wells (not shown in FIG. **2**A) can also be formed in both CMOS region **202** and bipolar region **204** of semiconductor substrate **201**. For example, another CMOS N well can be formed in semiconductor substrate **201** adjacent to CMOS P well **206**, where the CMOS N well and the CMOS P well can be utilized to respectively form a P-channel field-effect transistor (PFET) and an NFET (e.g., NFET **209**) of a CMOS device.

Referring to FIG. **2**B, structure **282** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **182** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As illustrated in FIG. **2**B, structure **282** includes gate electrode **211**, lightly doped source region **213***a*, lightly doped drain region **213***b*, common spacer oxide layer **212** and common spacer nitride layer **214**. In structure **282**, gate electrode **211** of NFET **209** is formed over CMOS P well **206**. An oxide layer may be formed between gate electrode **211** and CMOS P well **206**. Lightly doped source region **213***a* and lightly doped drain region **213***b* may be formed in CMOS P well **206** adjacent to gate electrode **211**. For example, lightly doped source region **213***a* and lightly doped drain region **213***b* may include lightly doped N type dopant. Common spacer oxide layer **212** and common spacer nitride layer **214** are successively formed on top surface **218** of semiconductor substrate **201** in CMOS region **202** and bipolar region **204**. Common spacer oxide layer **212** can include tetraethylorthosilicate ("TEOS") oxide. Common spacer nitride layer **214** can include silicon nitride. Common spacer oxide layer **212** and/or common spacer nitride layer **214** can be formed over CMOS region **202** and bipolar region **204** of semiconductor substrate **201** by using a chemical vapor deposition ("CVD") process or other appropriate processes. As shown in FIG. **2**B, in CMOS region **202**, common spacer oxide layer **212** and common spacer nitride layer **214** also cover gate electrode **211** of NFET **209**.

Referring to FIG. **2**C, structure **283** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **183** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As shown in FIG. **2**C, structure **283** includes spacer clear region **216**, sub-collector **220** and selectively implanted collector (SIC) or collector **234** of PNP device **207** formed in spacer clear region **216**. As illustrated in FIG. **2**C, spacer clear masking layer **215** is formed over common spacer nitride layer **214** and patterned to define spacer clear region **216** in PNP region **204***b* for PNP device **207**. Spacer clear

masking layer **215** may include photoresist or other appropriate masking material. The portions of common spacer nitride layer **214** and common spacer oxide layer **212** not covered by spacer clear masking layer **215** are removed by, for example, using an etching process to expose top surface **218** of semiconductor substrate **201**. High energy spacer clear implant **219**, such as high energy boron dopant or other appropriate P type high energy dopant, is implanted in semiconductor substrate **201** through top surface **218** in spacer clear region **216**, thereby forming sub-collector **220** of PNP device **207**, while spacer clear masking layer **215** protects the rest of the semiconductor substrate. As spacer clear masking layer **215** is still in place, SIC **234** having a highly p-doped local collector implant, which is closer to an interface between the sub-collector and the base of PNP device **207**, is also formed.

As further illustrated in FIG. **2**C, the P type implant in CMOS P well **210** in PNP region **204***b* may be utilized as the extrinsic collector contact implant for PNP device **207**. As such, CMOS P well **210** operates as collector sinker **224** for PNP device **207**. Sub-collector **220**, having high energy spacer clear implant **219**, and collector sinker **224**, having a heavily doped P type implant, may be in direct physical contact with and electrically connected to each other in overlapped region **222**. Sub-collector **220** and collector sinker **224** may have substantially the same depth below top surface **218** in semiconductor substrate **201**. Sub-collector **220** and collector sinker **224** form a direct electrical path for external connection for sub-collector **220** of PNP device **207**. As such, a buried sub-collector layer in a conventional process flow can be avoided in PNP device **207**. Consequently, masking layers required for forming the buried sub-collector layer and the associated implanting actions are also avoided.

Referring to FIG. **2**D, structure **284** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **184** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As shown in FIG. **2**D, structure **284** includes N type SiGe layer **226** formed on top surface **218** of semiconductor substrate **201** in spacer clear region **216** and on common spacer nitride layer **214** over other regions of semiconductor substrate **201**. As illustrated in FIG. **2**D, after spacer clear masking layer **215** is removed, N type SiGe layer **226** is formed over CMOS region **202** and bipolar region **204** of semiconductor substrate **201**, including spacer clear region **216**. In the present implementation, N type SiGe layer **226** may be epitaxially grown over the exposed top surface **218** of semiconductor substrate **201** in spacer clear region **216**. N type SiGe layer **226** forms a base for PNP device **207** in spacer clear region **216**. In another implementation, N type SiGe layer **226** may have a graded structure. For example, grading the concentration of germanium in a silicon-germanium base builds into a bipolar device an electric field, which accelerates the carriers across the base, thereby increasing the speed of the heterojunction bipolar device compared to a silicon-only device. For example, a reduced pressure chemical vapor deposition technique, or RPCVD, may be used to fabricate a controlled grading of germanium concentration across the base layer.

It is noted that, up to action **184** of flowchart **100**, the formation of sub-collector **220** and N type SiGe layer **226** as the base for PNP device **207** can be interchanged with the formation of a sub-collector and a base for NPN device **205**, by implanting dopants with reversed polarities in each of corresponding regions. For example, instead of forming sub-collector **220** and N type SiGe layer **226** for PNP device **207**, a spacer clear region may be formed in NPN device **205**, a vertical NPN collector implant may be performed, and a P type SiGe layer may be deposited over semiconductor substrate **201** to form a P type SiGe base for NPN device **205**.

Referring to FIG. **2**E, structure **285** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **185** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As shown in FIG. **2**E, structure **285** includes PNP emitter window **232** formed above SIC **234** of PNP device **207** in PNP region **204***b*. As illustrated in FIG. **2**E, PNP base oxide layer **228** and undoped furnace poly layer **230** are formed over N type SiGe layer **226** covering an entire top surface thereof. PNP emitter window **232** is formed in undoped furnace poly layer **230** and PNP base oxide layer **228**, and aligned with SIC **234** below. In one implementation, PNP emitter window **232** can be formed by depositing a mask over undoped furnace poly layer **230** to define an emitter window opening above SIC **234**, and removing portions of undoped furnace poly layer **230** and PNP base oxide layer **228** by using an appropriate etching process to extend the emitter window opening to a top surface N type SiGe layer **226**. In another implementation, PNP emitter window **232** may extend to a top surface of PNP base oxide layer **228**. In one implementation, an optional organic antireflection coating layer (not explicitly shown in FIG. **2**E) may be formed over undoped furnace poly layer **230** before the formation of PNP emitter window **232**. The organic antireflection coating layer may enhance photolithographic control over the formation of PNP emitter window **232**, and may be removed before any further processing action.

Referring to FIG. **2**F, structure **286** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **186** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As shown in FIG. **2**F, structure **286** includes spacer clear region **238**, sub-collector **240** and selectively implanted collector (SIC) or collector **244** in NPN region **204***a* for NPN device **205**. As illustrated in FIG. **2**F, spacer clear masking layer **236** is formed over undoped furnace poly layer **230** to define spacer clear region **238** in NPN region **204***a* for NPN device **205**. Spacer clear masking layer **236** may include photoresist or other appropriate masking material. The portions of undoped furnace poly layer **230**, PNP base oxide layer **228**, N type SiGe layer **226**, common spacer nitride layer **214** and common spacer oxide layer **212** not covered by spacer clear masking layer **236** are removed by, for example, using an etching process to expose a portion of top surface **218** of semiconductor substrate **201** in spacer clear region **238**. High energy spacer clear implant **239**, such as high energy phosphorous dopant or other appropriate N type high energy dopant, is implanted in semiconductor substrate **201** in spacer clear region **238**, thereby forming sub-collector **240** of NPN device **205**. While spacer clear masking layer **236** is still on the semiconductor substrate, SIC **244** having a highly N-doped local collector implant, which is closer to an interface between the sub-collector and the base of NPN device **205**, is also formed.

As further illustrated in FIG. **2**F, the N type implant in CMOS N well **208** in NPN region **204***a* may be utilized as the extrinsic collector contact implant for NPN device **205**. As such, CMOS N well **208** operates as collector sinker **248** for NPN device **205**. Sub-collector **240** for NPN device **205** is spaced from and electrically insulated from collector sinker **224** of PNP device **207**. On an opposite side, sub-collector **240** having high energy spacer clear implant **239**

and collector sinker **248** having a heavily doped N type implant, may be in direct physical contact with and electrically connected to each other with each other in overlapped region **242**. Sub-collector **240** and collector sinker **248** may have substantially the same depth below top surface **218** in semiconductor substrate **201**. Sub-collector **240** and collector sinker **248** form a direct electrical path for external connection for sub-collector **240** of NPN device **205**. As such, a buried sub-collector layer in a conventional process flow can be avoided in NPN device **205**. Consequently, masking layers required for forming the buried sub-collector layer and the associated implanting actions are also avoided.

Referring to FIG. **2**G, structure **287** illustrates a cross-sectional view of a portion of a semiconductor device after completion of action **187** in flowchart **100** of FIG. **1**, according to one implementation of the present disclosure. As shown in FIG. **2**G, structure **287** includes NFET **209** in CMOS region **202**, NPN device **205** in NPN region **204***a*, and PNP device **207** in PNP region **204***b*. Specifically, P type base **250***a* and N type emitter **258***a* of NPN device **205**, P type SiGe emitter **250***b* of PNP device **207**, and source region **274***a* and drain region **274***b* of NFET **209** are formed in action **187**.

As illustrated in FIG. **2**G, NFET **209** includes CMOS P well **206**, gate electrode **211**, common spacer oxide layer **212**, spacers **214***a* and **214***b*, lightly doped source region **213***a*, lightly doped drain region **213***b*, source region **274***a*, and drain region **274***b*. CMOS P well **206** is situated between isolation regions **203***a* and **203***b* in CMOS region **202**. Gate electrode **211** is situated over CMOS P well **206** on common spacer oxide layer **212** in CMOS region **202**. For example, gate electrode **211** includes polycrystalline silicon. Spacers **214***a* and **214***b* are situated adjacent to gate electrode **211** and over CMOS P well **206** in CMOS region **202**. In the present implementation, spacers **214***a* and **214***b* include silicon nitride.

In other implementations, spacer **214***a* and **214***b* can include silicon oxide or other appropriate dielectric material. Spacer **214***a* and **214***b* can be formed by depositing a conformal common spacer layer, such as a silicon oxide and/or silicon nitride layer, over CMOS region **202** and bipolar region **204** of semiconductor substrate **201**. The layer of dielectric material can then be etched back using an anisotropic etching process to form spacers **214***a* and **214***b*. Lightly doped source region **213***a* and lightly doped drain region **213***b* are formed adjacent to gate electrode **211** in CMOS P well **206** in CMOS region **202**. Lightly doped source region **213***a* and lightly doped drain region **213***b* include lightly doped N type regions. Source region **274***a* and drain region **274***b* are formed in CMOS region **202** of semiconductor substrate **201**. Source region **274***a* is situated in CMOS P well **206** between isolation region **203***a* and lightly doped source region **213***a*. Drain region **274***b* is situated in CMOS P well **206** between isolation region **203***b* and lightly doped drain region **213***b*.

As illustrated in FIG. **2**G, NPN device **205** includes N type emitter **258***a*, NPN emitter spacers **270***a* and **270***b*, P type base **250***a*, SIC **244**, N type sub-collector **240**, collector sinker **248** and collector contact **275***a*. In the present implementation, NPN device **205** is a vertical heterojunction bipolar transistor. N type emitter **258***a* is situated between NPN emitter spacers **270***a* and **270***b* and over P type base **250***a* in NPN region **204***a*. N type emitter **258***a* can include N type polycrystalline silicon, which can be doped with phosphorus or other appropriate N type dopant. Heavily doped extrinsic base regions **264***a* and **264***b* are situated in P type base **250***a* adjacent to N type emitter **258***a* in semiconductor substrate **201** in NPN region **204***a*. Sub-collector **240** and SIC **244** of NPN device **205** are formed in NPN region **204***a*.

As illustrated in FIG. **2**G, sub-collector **240** and collector sinker **248** may have substantially the same depth below top surface **218** in semiconductor substrate **201**. Sub-collector **240** having an N type high energy spacer clear implant partially overlaps collector sinker **248** having heavily doped N type implant in overlapped region **242**. Sub-collector **240** and collector sinker **248** form a direct electrical path for external connection using collector contact **275***a* of NPN device **205**. In the present implementation, CMOS P well **206** for NFET **209** and collector sinker **248** formed using CMOS N well **208** form p-n junction **246** in semiconductor substrate **201**, where p-n junction **246** provides electrical isolation between NFET **209** and NPN device **205** in semiconductor substrate **201**. As such, CMOS P well **206** for NFET **209** and collector sinker **248** of NPN device **205** need not be placed apart from each other, thereby saving usable space on semiconductor substrate **201**.

As illustrated in FIG. **2**G, PNP device **207** includes P type SiGe emitter **250***b*, PNP emitter spacers **270***c* and **270***d*, N type SiGe base **226***a*, SIC **234**, P type sub-collector **220**, collector sinker **224** and collector contact **275***b*. In the present implementation, PNP device **207** is a vertical heterojunction bipolar transistor. P type SiGe emitter **250***b* is situated between PNP emitter spacers **270***c* and **270***d* and over N type SiGe base **226***a* in PNP region **204***b*. Heavily doped extrinsic base regions **269***a* and **269***b* are situated in N type SiGe base **226***a* adjacent to P type SiGe emitter **250***b* in PNP region **204***b*. Sub-collector **220** and SIC **234** of PNP device **207** are formed in PNP region **204***b*.

As illustrated in FIG. **2**G, sub-collector **220** and collector sinker **224** may have substantially the same depth below top surface **218** in semiconductor substrate **201**. Sub-collector **220** having a P type high energy spacer clear implant partially overlaps collector sinker **224** having a heavily doped P type implant in overlapped region **222**. Sub-collector **220** and collector sinker **224** form a direct electrical path for external connection using collector contact **275***b* of PNP device **207**. In the present implementation, collector sinker **224** of PNP device **207** and sub-collector **240** of NPN device **205** are spaced apart from each other to provide electrical isolation between PNP device **207** and NPN device **205**. In another implementation, collector sinker **224** of PNP device **207** and sub-collector **240** of NPN device **205** may be placed immediately adjacent to each other.

Although FIGS. **2**A-**2**G illustrate the formations of CMOS P well **206**, CMOS N well **208**, CMOS P well **210**, NFET **209**, NPN device **205** and PNP device **207** in the present implementation, it should be understood that, in another implementation according to the present inventive concepts, the above-mentioned regions can be interchanged with the formations of a CMOS N well, CMOS P well, CMOS N well, a PFET, a PNP device and an NPN device, by implanting dopants with reversed polarities in each of the corresponding regions.

Thus, the present inventive concepts utilize CMOS N and P wells in a bipolar region of a semiconductor substrate as collector sinkers for complementary bipolar devices, where each of the collector sinkers is connected to a sub-collector, having a high energy implant, for a respective bipolar device in the same semiconductor substrate. The advantages of the present inventive concepts may include reduced cost of fabrication due to the shared well implants, the elimination

of one or more process steps related to conventional buried sub-collector layer fabrication and isolation structures, and reduced collector resistance.

From the above description it is manifest that various techniques can be used for implementing the concepts described in the present application without departing from the scope of those concepts. Moreover, while the concepts have been described with specific reference to certain implementations, a person of ordinary skill in the art would recognize that changes can be made in form and detail without departing from the scope of those concepts. As such, the described implementations are to be considered in all respects as illustrative and not restrictive. It should also be understood that the present application is not limited to the particular implementations described above, but many rearrangements, modifications, and substitutions are possible without departing from the scope of the present disclosure.

The invention claimed is:

1. A bipolar complementary-metal-oxide-semiconductor (BiCMOS) device comprising:

a CMOS device in a CMOS region of a substrate;

a first well in said CMOS region;

an NPN bipolar device in a bipolar region of said substrate;

a second well in said bipolar region;

a sub-collector of said NPN bipolar device reaching a top surface of said substrate, said sub-collector surrounding a selectively implanted collector;

said second well being a collector sinker, said collector sinker being laterally adjacent and electrically connected to said sub-collector of said NPN bipolar device in a laterally overlapping region;

wherein said first well in said CMOS region and said collector sinker in said bipolar region form a p-n junction to provide electrical isolation between said CMOS device and said NPN bipolar device;

said collector sinker being electrically connected to a collector contact;

said sub-collector not extending vertically below said collector sinker.

2. The BiCMOS device of claim **1**, wherein said substrate is a P type silicon substrate.

3. The BiCMOS device of claim **1**, further comprising a third well in said bipolar region, wherein said first well and said third well have the same conductivity type.

4. The BiCMOS device of claim **1**, further comprising a PNP bipolar device having a sub-collector, said sub-collector of said PNP bipolar device being electrically connected to a third well in said bipolar region.

5. The BiCMOS device of claim **4**, wherein said third well is a collector sinker for said PNP bipolar device.

6. The BiCMOS device of claim **4**, wherein said PNP bipolar device comprises a base over said sub-collector of said PNP bipolar device, said base of said PNP bipolar device comprising silicon germanium (SiGe).

7. The BiCMOS device of claim **4**, wherein said third well is a P well.

8. The BiCMOS device of claim **1**, wherein said CMOS device is an N-channel field-effect transistor (NFET).

9. The BiCMOS device of claim **1**, wherein said first well is a P well, and said collector sinker is an N well.

10. A bipolar complementary-metal-oxide-semiconductor (BiCMOS) device comprising:

a CMOS device in a CMOS region of a substrate;

a first well in said CMOS region;

an NPN bipolar device in a bipolar region of said substrate;

a second well in said bipolar region;

a sub-collector of said NPN bipolar device reaching a top surface of said substrate, said sub-collector surrounding a selectively implanted collector;

said second well being laterally adjacent and electrically connected to said sub-collector of said NPN bipolar device in a laterally overlapping region;

wherein said first well in said CMOS region and said second well in said bipolar region form a p-n junction to provide electrical isolation between said CMOS device and said NPN bipolar device;

said second well being electrically connected to a collector contact;

said sub-collector not extending vertically below said second well.

11. The BiCMOS device of claim **10**, wherein said substrate is a P type silicon substrate.

12. The BiCMOS device of claim **10**, further comprising a third well in said bipolar region, wherein said first well and said third well have the same conductivity type.

13. The BiCMOS device of claim **10**, further comprising a PNP bipolar device having a sub-collector, said sub-collector of said PNP bipolar device being electrically connected to a third well in said bipolar region.

14. The BiCMOS device of claim **13**, wherein said third well is a collector sinker for said PNP bipolar device.

15. The BiCMOS device of claim **13**, wherein said PNP bipolar device comprises a base over said sub-collector of said PNP bipolar device, said base of said PNP bipolar device comprising silicon germanium (SiGe).

16. The BiCMOS device of claim **13**, wherein said third well is a P well.

17. The BiCMOS device of claim **10**, wherein said CMOS device is an N-channel field-effect transistor (NFET).

18. The BiCMOS device of claim **10**, wherein said first well is a P well, and said second well is an N well.

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